### INTEGRATED CIRCUITS

# DATA SHEET

DataSheet4U.com

DataShe

## TDA8720T; TDA8720M I<sup>2</sup>C-bus programmable modulator for negative video modulation and FM sound

Objective specification File under Integrated Circuits, IC02 November 1993

## **Philips Semiconductors**





### **TDA8720T; TDA8720M**

#### **FEATURES**

- Video amplifier with clamping circuit, white clip circuit and automatic gain control circuit which allows handling of video signals between 0.7 and 1.4 V (p-p)
- · FM sound modulator
- Asymmetrical and symmetrical RF outputs
- Symmetrical RF oscillator covering more than 20 channels with only a few external components
- I2C-bus receiver for frequency setting and test-mode selection
- · Phase-locked-loop frequency synthesizer
- · On-chip power supply regulator.

### **APPLICATIONS**

- · Video recorders
- Video generators
- · Cable converters.



### **GENERAL DESCRIPTION**

The TDA8720 is a programmable modulator which has been designed to generate an RF TV channel from a baseband video signal and a baseband audio signal in applications of negative video and FM sound standards.

It is especially suitable for video generators, video recorders and cable converters. The picture carrier frequency is set exactly to the correct channel frequency by a PLL synthesizer which is programmed in accordance with the I2C-bus format.

### et4U.com

### **QUICK REFERENCE DATA**

DataSheet4U.com

V<sub>DD</sub> = 5 V and T<sub>amb</sub> = 25 °C after the IC has reached thermal equilibrium; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{DDA}, V_{DDD}$	analog and digital supply voltage		4.5	5.0	5.5	V
I <sub>DD</sub>	total supply current		41	51	61	mA
f <sub>SYN</sub>	synthesizer frequency range		-	-	900.25	MHz
V <sub>19(p-p)</sub>	video input voltage level (peak-to-peak value)		0.7	1.0	1.4	V
V <sub>RF</sub>	RF output voltage level	f = 471.25 MHz	75	78	82	dΒμV
	asymmetrical on a 75 $\Omega$ load	f = 663.25 MHz	73	76	80	dBμV
m	video modulation depth	colour bars pattern	_	83	_	%
V <sub>1(rms)</sub>	maximum audio input voltage level (RMS value)	before pre-emphasis filter	_	0.5	-	V
Δf	FM deviation in audio subcarrier	$f = 400 \text{ Hz}$ ; $V_1 = 0.5 \text{ V(RMS)}$ ; before pre-emphasis filter	_	25	_	kHz

#### **ORDERING INFORMATION**

EXTENDED TYPE		PACKAGE						
NUMBER	PINS	PIN POSITION	MATERIAL	CODE				
TDA8720T	20	SO20L	plastic	SOT163A				
TDA8720M	20	SSOP20	plastic	SOT266A				

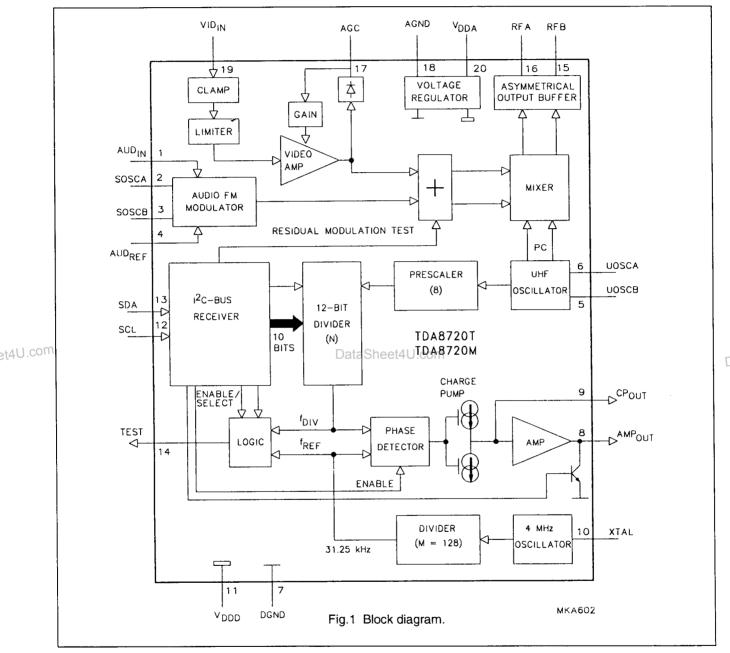
DataSheet4U.com

November 1993

www.DataSheet4U.com



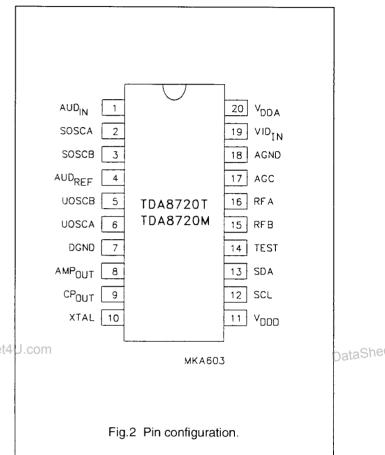
## TDA8720T; TDA8720M



## TDA8720T; TDA8720M

### **PINNING**

SYMBOL	PIN	DESCRIPTION
AUD <sub>IN</sub>	1	audio input
SOSCA	2	sound oscillator A
SOSCB	3	sound oscillator B
AUD <sub>REF</sub>	4	audio reference input
UOSCB	5	UHF oscillator B
UOSCA	6	UHF oscillator A
DGND	7	digital ground
AMP <sub>OUT</sub>	8	tuning amplifier output
CP <sub>OUT</sub>	9	charge pump output
XTAL	10	crystal oscillator
V <sub>DDD</sub>	11	digital supply voltage
SCL	12	serial clock ( I <sup>2</sup> C bus )
SDA	13	serial data ( I2C bus )
TEST	14	test output
RFB	15	RF output B
RFA	16	RF output A DataShee
AGC	17	automatic gain control of video amplifier
AGND	18	analog ground
VID <sub>IN</sub>	19	video input
$V_{DDA}$	20	analog supply voltage



#### Philips Semiconductors

## I<sup>2</sup>C-bus programmable modulator for negative video modulation and FM sound

### TDA8720T; TDA8720M

#### **FUNCTIONAL DESCRIPTION**

The TDA8720 is a programmable modulator which can be divided into two main blocks:

- a modulator for negative video modulation and FM sound TV standards
- · a programmable PLL frequency synthesizer

The video part of the modulator consists of:

- a clamping circuit which sets the internal reference voltage level to the bottom of the synchronizing pulse.
- a limiter which clips strong signals higher than 1.5 V to avoid overmodulation.
- a peak white detector which measures the amplitude of the top white level and then controls the gain of the video amplifier. The capacitor for the detector, C17 (see Fig.5) is external and may therefore be adapted in the application.
- a video amplifier with variable gain which delivers a constant amplitude when the external video signal is within the range 0.7 to 1.4 V.

The audio part of the modulator consists of an FM sound modulator. The frequency of the sound subcarrier is set in the application by external components C3, L3 and R3 (see Fig.5).

The RF part of the modulator consists of:

 an oscillator which operates at the required picture carrier frequency. The range of the oscillator is determined by the application. In our reference measuring set-up, we guarantee a range of 471.25 to 663.25 MHz, (channel 21 to channel 45 of G standard) with L5, C5, C6 and D5 (see Fig.5).  an RF mixer which combines the video signal and the sound subcarrier to build a baseband TV channel.
 The baseband signal is then mixed with the oscillator signal to produce the RF TV channel. The mixer has two outputs which can be used as either two independent asymmetrical outputs or as one symmetrical output.

The channel frequency is set by a programmable PLL frequency synthesizer.

The PLL frequency synthesizer controls the oscillator frequency in accordance with the following formula:  $f_{OSC} = 8 \times N \times f_{REF}$ 

#### Where:

- fosc is the local oscillator frequency
- N is a 12-bit dividing number (10 bits are programmable)
- f<sub>BFF</sub> is the crystal frequency (f<sub>XTAL</sub>) divided by 128.

The circuit therefore allows a minimum step of 250 kHz internally and a software controlled step of 1 MHz because only 10 bits are programmable. When the PLL loop is locked, both inputs of the phase comparator are equal. This produces the following formula:

$$f_{DIV} = f_{OSC} / 8 / N = f_{XTAL} / 128 = f_{REF}$$

During the test mode operation,  $f_{DIV}$  and  $f_{REF}$  can be monitored on the Test output pin (pin 14).

#### Software information

The synthesizer is controlled via a two-wire l<sup>2</sup>C-bus receiver. For programming, the address byte (C8 in Hex format) has to be sent first. One or two data bytes are then used to set the 10 programmable bits of the dividing number N and the test bits (see Table 1).

Table 1 Data format.

BYTE	MSB							LSB	
address C8	1	1	0	0	1	0	0	0	ACK
data byte 1	0	b11	b10	b9	b8	b7	b6	b5	ACK
data byte 2	1	test	test1	test2	not used	b4	b3	b2	ACK

Where: ACK is the acknowledge bit, and bits b2 to b11 are the 10 programmable bits of N. b1 = 0, b0 = 1 are set by internal hardware.

test, test1 and test2 are 3 bits used for test purpose (see Table 5).

www.DataSheet4U.com

DataShe

DataSheet4U.com

et4U.com

November 1993

TDA8720T; TDA8720M

The bits b2 to b11 are programmable and represent the integer part of the frequency in MHz. b1 and b0 are fixed internally to 0 and 1 respectively to obtain the added 0.25 MHz, common to most TV channels (see Table 2).

Table 2 Structure of the dividing number N.

BITS	b11	b10	b9	b8	b7	b6	b5	b4	b3	b2	b1	b0
frequency in MHz	512	256	128	64	32	16	8	4	2	1	0.5	0.25

#### Note to Table 2

Bits b1 and b0 are not programmable

 $f_{OSC} = 512 \times b11 + 256 \times b10 + .... + b2 \times 1 + 0.25$  (in MHz)

**Table 3** Dividing number N to program channel 21 = 471.25 MHz.

BITS	b11	b10	b9	b8	b7	b6	b5	b4	b3	b2	b1	b0
value	0	1	1	1	0	1	0	1	1	1	0	1
frequency in MHz	0	256	128	64	0	16	0	4	2	1	0	0.25

#### Note to Table 3

et4U.com

Bits b1 and b0 and their values 0 and 1 are not programmable

DataSheet4U.com

**Table 4** Content of the data bytes to program channel 21 = 471.25 MHz.

BYTE	MSB							LSB	
address C8	1	1	0	0	1	0	0	0	ACK
data byte 1	0	0	1	1	1	0	1	0	ACK
data byte 2	1	0	0	0	0	1	1	1	ACK

It is possible to change only one data byte. The circuit will recognize which one is received with the value of MSB, 0 for data byte 1 and 1 for data byte 2. It is possible to change the frequency by 1 MHz using data byte 2. It is relatively simple to increment the channel frequency when its frequency width is 8 MHz by simply incrementing data byte 1.

Table 5 Test modes.

TEST	TEST 1	TEST 2	OPERATIONAL MODE	
0	0	Х	normal operation	
0	1	Х	balance test	
1	0	0	f <sub>REF</sub> output	
1	0	1	high impedance test	
1	1	0	f <sub>DIV</sub> output	
1	1	1	phase detector disabled	

Where X = 0 or 1

DataShe

DataSheet4U.com

TDA8720T; TDA8720M

The high impedance mode may be used to control the RF tank circuit to test the oscillator with an external tuning voltage. In this mode, the phase detector is disabled and the external transistor of the tuning amplifier is switched OFF. The AMP output (pin 8) is LOW (<200 mV).

In the balance test mode, overmodulation is present in the RF mixer to allow the measurement of the parasitic residual modulation.

In the f<sub>BEE</sub> and f<sub>DIV</sub> modes, the reference frequency (f<sub>BEE</sub>) in the phase comparator or the divided RF oscillator frequency (f<sub>DIV</sub>) is available at the test pin.

In the phase detector disabled mode, it is possible to measure the leakage current at the input of the tuning amplifier (pin 9).

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V <sub>DDA</sub> , V <sub>DDD</sub>	analog and digital supply voltage	-0.3	+6	V
$V_{DDA}, V_{DDD}$	analog and digital operating voltage	4.5	5.5	V
T <sub>stg</sub>	storage temperature	-40	+125	°C
V <sub>max</sub>	maximum voltage on all pins	-0.3	V <sub>DD</sub>	V
T <sub>amb</sub>	operating ambient temperature	-10	+80	°C

## et4U.com THERMAL RESISTANCE

DataSheet4U.com

SYMBOL	PARAMETER	THERMAL RESISTANCE
R <sub>th j-a</sub>	from junction to ambient in free air	
(1)-4	SOT163A	85 K/W
	SOT266A	120 K/W

TDA8720T; TDA8720M

### **CHARACTERISTICS**

 $V_{DDA} = V_{DDD} = 5 \text{ V}; T_{amb} = 25 \text{ °C}; \text{ measured in circuit of Fig.5}; \text{ unless otherwise specified.}$ 

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	7
Supply		111		<u> </u>	<del></del>		1
$V_{DDA}$ , $V_{DDD}$	supply voltage		4.5	5.0	5.5	V	
I <sub>DDA</sub> , I <sub>DDD</sub>	supply current		41	51	61	mA	
Video chara	ecteristics					•	
I <sub>19</sub>	input current (AC)	V <sub>19</sub> = 2.6 V	_	11	-	μА	
V <sub>19(p-p)</sub>	input voltage level (peak-to-peak value)		0.7	1.0	1.4	V	
m	modulation depth	see Fig.3	76	83	89	%	
S/N video	signal-to-noise ratio	note 1	45	48	_	dB	
G <sub>diff</sub>	differential gain	note 2	_	4	8	%	1
$\Phi_{diff}$	differential phase	note 2	-	4	8	deg	7
Audio chara	acteristics		•	•	—· <b>1</b>		
Z <sub>1</sub>	input impedance		35	70	105	kΩ	
V <sub>1(rms)</sub>	maximum audio input voltage level (RMS value)	before pre-emphasis	_	0.5	_	V	
Δm	modulation deviation	$f_{AUD} = 400 \text{ Hz};$ $V_1 = 0.5 \text{ V (RMS)}; \text{ before}$ pre-emphasis filter	20	25	30	kHz	Da
THD	total harmonic distortion	$\Delta f = 50 \text{ kHz}; f_{AUD} = 6.3 \text{ kHz}$	_	1.8	3.0	%	
S/N audio	signal-to-noise ratio	CCIR filter 468 - 3; $f_{AUD} = 1$ kHz; $V_1 = 0.5$ V (RMS); before pre-emphasis filter	42	52	_	dB	
SVR	sound carrier relative to picture carrier (sync RMS)	no audio signal; FM = 5.5 MHz; pin 19 connected to ground via 10 kΩ resistor	-18	-14	-10	dB	
Channel ch	aracteristics			- <del>1</del> .	•		1
f <sub>RF</sub>	frequency range	related to tank circuit; see Fig.5	471.25	T-	663.25	MHz	1
f <sub>step</sub>	frequency step		_	1	-	MHz	1
V <sub>15, 16</sub>	output voltage level at pins	f = 471.25 MHz	75	78	82	dΒμV	7
	15 and 16; pin 19 connected to ground via 10 k $\Omega$ resistor; asymmetrical output loaded with 75 $\Omega$	f = 663.25 MHz	73	76	80	dΒμV	
N <sub>SPO</sub>	spurious noise outside channel	note 3	_	-62	_	dBc	
N <sub>SPI</sub>	spurious noise inside channel		_	- 50	-	dBc	
RF <sub>sh</sub>	RF second harmonic level	asymmetrical output	-	-30	_	dBc	
SC <sub>th</sub>	sound carrier third harmonic level		-	-57	-	dBc	
IM	chrominance beat	note 4	_	-62	-58	dBc	
	<del></del>	<u> </u>	<del></del>				_

et4U.com

## TDA8720T; TDA8720M

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Synthesizer	characteristics					
f <sub>XTAL</sub>	crystal frequency		_	4	_	MHz
f <sub>REF</sub>	reference frequency		_	31.25		kHz
f <sub>SYNT</sub>	synthesizer frequency			_	900.25	MHz
Charge pum	p output (pin 9)					
l <sub>9</sub>	output current		_	±100	_	μΑ
$V_9$	output voltage	in lock	1.5	_	2.5	V
I <sub>IL</sub>	off-stage leakage current	V <sub>9</sub> = 2 V; test = 1; test1 = 1; test2 = 1		_	10	nA
Amplifier ou	itput (pin 8)					
G	amplifier current gain	$V_9 = 2 \text{ V}; I_8 = 10 \mu\text{A}$		4000	<u> </u>	
V <sub>8</sub>	output saturation voltage	$V_g = 0 \text{ V}$ ; test = 1; test1 = 0; test2 =1	_	140	200	mV
l <sup>2</sup> C-bus rece	eiver characteristics					
V <sub>IH</sub>	HIGH level Input voltage SDA and SCL		3	_	5.5	V
V <sub>IL</sub>	LOW level Input voltage SDA and SCL	DataSheet4U.com	0	-	1.5	V
I <sub>iH</sub>	HIGH level Input current SDA and SCL	$V_{IH} = 5 \text{ V}; V_{DDA}, V_{DDD} = 0 \text{ to } 5 \text{ V}$	-		+10	μΑ
اير	LOW level Input current SDA and SCL	$V_{IL} = 0 \text{ V}; V_{DDA}, V_{DDD} = 0 \text{ to } 5 \text{ V}$	-10	-	-	μА
V <sub>OL</sub>	LOW level output voltage SDA during acknowledge pulse	I <sub>IL</sub> = 3 mA	_	_	0.4	V

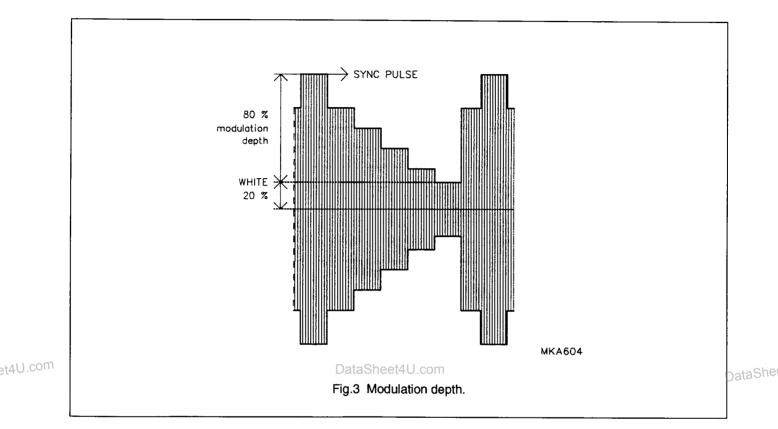
#### **Notes**

- 1. Signal-to-noise ratio: ratio between the CCIR 17 line bar amplitude and the RMS value of the noise on a black line (line 22 or 335). Measurement is unweighted.
- 2. The differential phase and gain are measured for G standard on CCIR 330 line.
- 3. Except for the harmonics of the RF oscillator frequency and the combinations between the RF oscillator and the sound oscillator frequency; (f<sub>RF</sub> + 2f<sub>s</sub>, 2f<sub>RF</sub> + f<sub>s</sub>......).
- 4. Chrominance beat: measured with a video signal of 1 V(p-p) with a chrominance carrier of 400 mV(p-p) filtered around 1.07 MHz with the filter illustrated in Fig.4. Following this method the chrominance beat can be seen on a spectrum analyser.

et4U.com

www.DataSheet4U.com

## TDA8720T; TDA8720M



video generator

R1
75 Ω

P J DAB720

MKA605

Fig.4 Schematic of video filter for chrominance-beat measurement.

#### **HANDLING**

Inputs and outputs are protected against electrostatic discharge in normal handling. However, to be completely safe, it is desirable to take normal precautions appropriate to handling integrated circuits.

Every pin withstands the ESD test in accordance with MIL-STD-883C category B (2000 V).

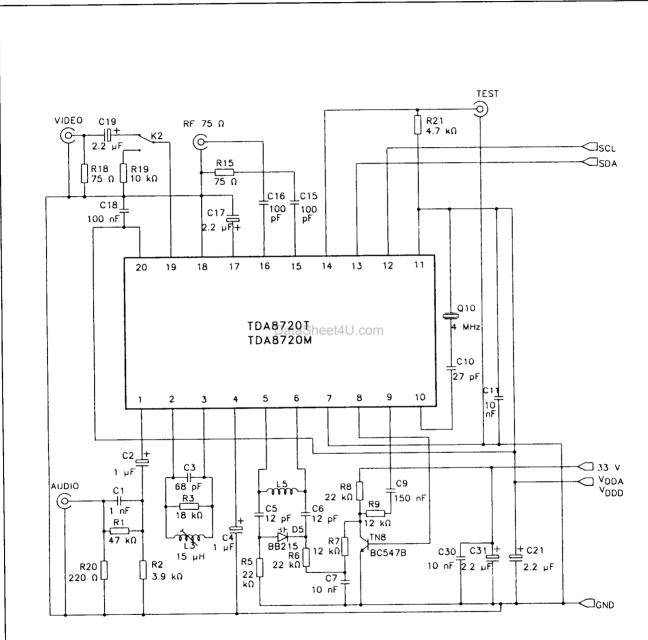
Every pin withstands the ESD test in accordance with Philips Semiconductors Machine Model 0  $\Omega$ , 200 pF (200 V).

DataSheet4U.com

November 1993

## TDA8720T; TDA8720M

### **APPLICATION INFORMATION**



K2 : Switches the video input to input signal or to ground via a 10  $k\Omega$  resistor.

MKA606

L3 : To be adjusted for correct sound carrier (5.5 MHz for PAL G).

L5 : Air coil, 2.5 turns diameter 2 mm.

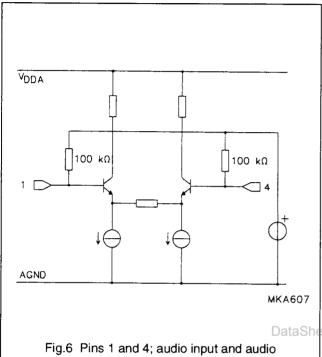
Fig.5 Reference measuring set-up for a G standard application.

DataSheet4U.com November 1993 www.DataSheet4U.com

DataShe

TDA8720T; TDA8720M

### INTERNAL PIN CONFIGURATION



reference.

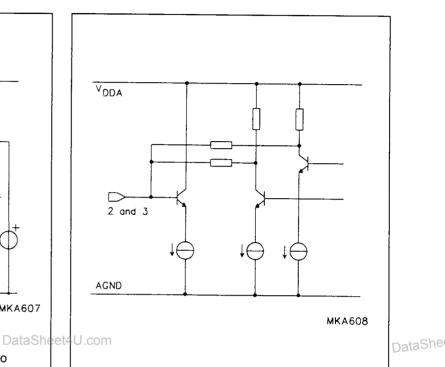
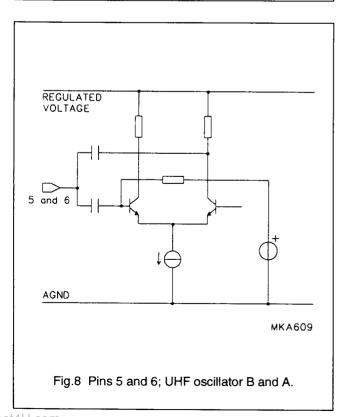
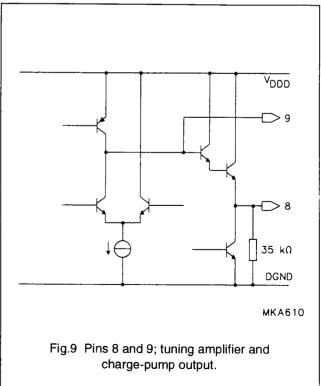


Fig.7 Pins 2 and 3; sound oscillator A and B.

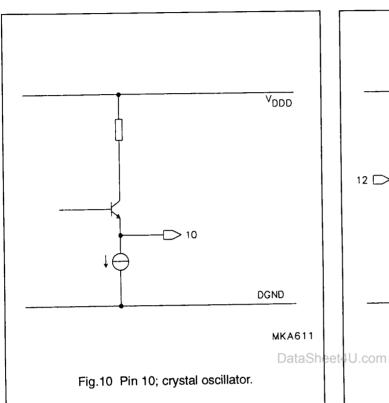




DataSheet4U.com November 1993

www.DataSheet4U.com

## TDA8720T; TDA8720M



VDDD

12 DGND

MKA612

WU.com

Fig.11 Pin 12; serial clock.

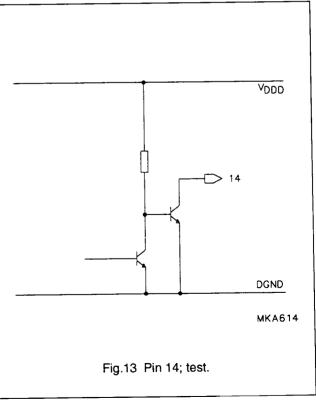
et4U.com

VDDD

13 DGND

MKA613

Fig.12 Pin 13; serial data.

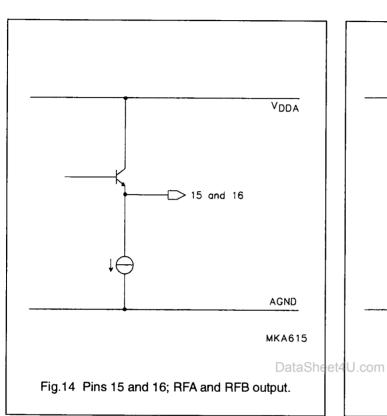


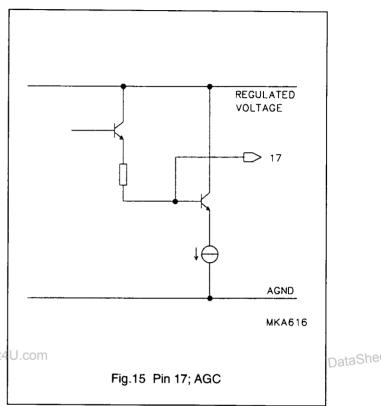
DataSheet4U.com

November 1993

www.DataSheet4U.com

## TDA8720T; TDA8720M





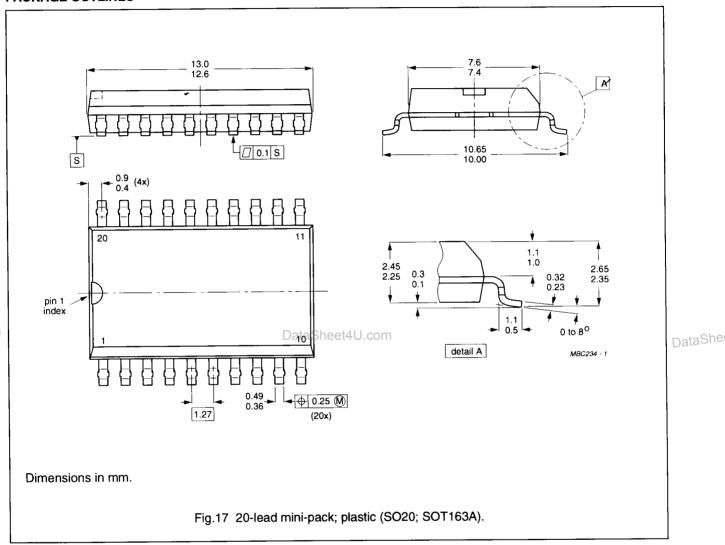
et4U.com

19 AGND
MKA617

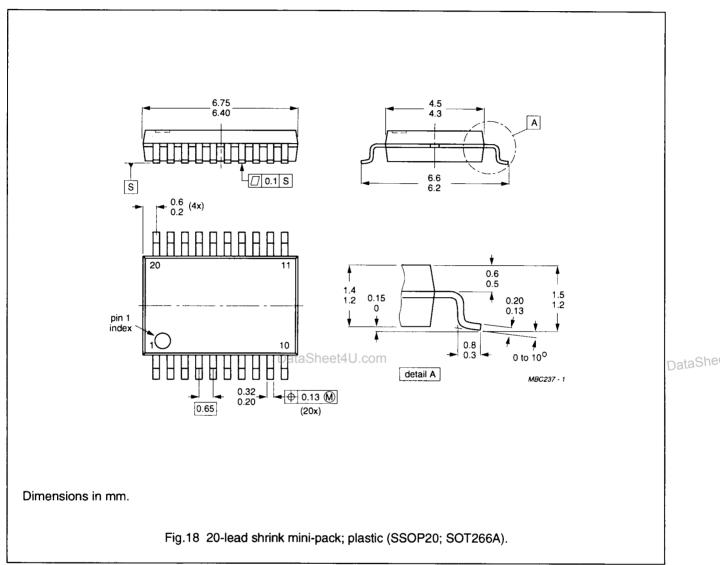
Fig.16 Pin 19; video input.

## TDA8720T; TDA8720M

### **PACKAGE OUTLINES**



## TDA8720T; TDA8720M



#### Philips Semiconductors

## I<sup>2</sup>C-bus programmable modulator for negative video modulation and FM sound

TDA8720T; TDA8720M

#### SOLDERING

#### Plastic mini-packs

By WAVE

During placement and before soldering, the component must be fixed with a droplet of adhesive. After curing the adhesive, the component can be soldered. The adhesive can be applied by screen printing, pin transfer or syringe dispensing.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder bath is 10 s, if allowed to cool to less than 150 °C within 6 s. Typical dwell time is 4 s at 250 °C.

A modified wave soldering technique is recommended using two solder waves (dual-wave), in which a turbulent wave with high upward pressure is followed by a smooth laminar wave. Using a mildly-activated flux eliminates the need for removal of corrosive residues in most applications.

et4U.com

By SOLDER PASTE REFLOW

DataSheet4U.com

Reflow soldering requires the solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the substrate by screen printing, stencilling or pressure-syringe dispensing before device placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt, infrared, and vapour-phase reflow. Dwell times vary between 50 and 300 s according to method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 min at 45 °C.

REPAIRING SOLDERED JOINTS (BY HAND-HELD SOLDERING IRON OR PULSE-HEATED SOLDER TOOL)

Fix the component by first soldering two, diagonally opposite, end pins. Apply the heating tool to the flat part of the pin only. Contact time must be limited to 10 s at up to 300 °C. When using proper tools, all other pins can be soldered in one operation within 2 to 5 s at between 270 and 320 °C. (Pulse-heated soldering is not recommended for SO packages.)

For pulse-heated solder tool (resistance) soldering of VSO packages, solder is applied to the substrate by dipping or by an extra thick tin/lead plating before package placement.

www.DataSheet4U.com

TDA8720T; TDA8720M

#### **DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later
Product specification	This data sheet contains final product specifications.
Limiting values	
more of the limiting values operation of the device at t	n accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and hese or at any other conditions above those given in the Characteristics sections of the Exposure to limiting values for extended periods may affect device reliability.
Application information	
Where application informat	ion is given, it is advisory and does not form part of the specification

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

et4U.com

DataSheet4U.com

DataShe

#### **PURCHASE OF PHILIPS 12C COMPONENTS**



Purchase of Philips I<sup>2</sup>C components conveys a license under the Philips' I<sup>2</sup>C patent to use the components in the I<sup>2</sup>C system provided the system conforms to the I<sup>2</sup>C specification defined by Philips. This specification can be ordered using the code 9398 393 40011.

DataSheet4U.com November 1993

**Argentina:** IEROD, Av. Juramento 1991 - 14.B, (1428) Buenos Aires, Tel. (541)786 7633, Fax. (541)786 9367

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113, Tel. (01)60 101-1236, Fax. (01)60 101-1211

Belgium: Postbus 90050, 5600 PB EINDHOVEN, The Netherlands,

Tel. (31)40 783 749, Fax. (31)40 788 399

**Brazil:** Rua do Rocio 220 - 5<sup>th</sup> floor, Suite 51, CEP: 04552-000-SÃO PAULO-SP, Brazil.

P.O. Box 7383 (01064-970).

Tel. (011)829-1166, Fax. (011)829-1849

Canada: INTEGRATED CIRCUITS: Tel. (800)234-7381, Fax. (708)296-8556 DISCRETE SEMICONDUCTORS: 601 Milner Ave,

SCARBOROUGH, ONTARIO, M1B 1M8

Tel. (0416)292 5161 ext. 2336, Fax. (0416)292 4477

Chile: Av. Santa Maria 0760, SANTIAGO, Tel. (02)773 816, Fax. (02)777 6730

Colombia: Carrera 21 No. 56-17, BOGOTA, D.E., P.O. Box 77621, Tel. (571)217 4609, Fax. (01)217 4549

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,

Tel. (032)88 2636, Fax. (031)57 1949

Finland: Sinikalliontie 3, SF-02630 ESPOO,

Tel. (9)0-50261, Fax. (9)0-520971

France: 4 rue du Port-aux-Vins, BP317,

92156 SURESNES Cedex Tel. (01)4099 6161, Fax. (01)4099 6427

**Germany:** P.O. Box 10 63 23, 20095 HAMBURG, Tel. (040)3296-0, Fax. (040)3296 213

**Greece:** No. 15, 25th March Street, GR 17778 TAVROS, Tel. (01)4894 339/4894 911, Fax. (01)4814 240

India: PEICO ELECTRONICS & ELECTRICALS Ltd.,

Components Dept., Shivsagar Estate, Block '

Dr. Annie Besant Rd., Worli, BOMBAY-400 018,

Tel. (022)4938 541, Fax. (022)4938 722

Indonesia: Philips House, Jalan H.R. Rasuna Said Kav. 3-4, P.O. Box 4252, JAKARTA 12950, Tel. (021)5201 122, Fax. (021)5205 189

Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. (01)640 000, Fax. (01)640 200

Italy: Viale F. Testi, 327, 20162-MILANO

Tel. (02)6752.1, Fax. (02)6752.3350

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKIO 108, Tel. (03)3740 5101, Fax. (03)3740 0570

Korea: (Republic of) Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. (02)794-5011, Fax. (02)798-8022

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR, Tel. (03)757 5511, Fax. (03)757 4880

Mexico: Philips Components, 5900 Gateway East, Suite 200, EL PASO, TX 79905, Tel. 9-5(800)234-7381, Fax. (708)296-8556 Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Tel. (040)78 37 49, Fax. (040)78 83 99

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,

Tel. (09)849-4160, Fax. (09)849-7811

Norway: Box 1, Manglerud 0612, OSLO, Tel. (22)74 8000, Fax. (22)74 8341

Pakistan: Philips Markaz, M.A. Jinnah Rd., KARACHI-3, Tel. (021)577 039, Fax. (021)569 1832

Philippines: PHILIPS SEMICONDUCTORS PHILIPPINES Inc. 106 Valero St. Salcedo Village, P.O. Box 911, MAKATI,

Metro MANILA, Tel. (02)810 0161, Fax. (02)817 3474 Portugal: Av. Eng. Duarte Pacheco 6, 1009 LISBOA Codex. Tel. (01)683 121, Fax. (01)658 013

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231, Tel. (65)350 2000, Fax. (65)251 6500 South Africa: 195-215 Main Road, Martindale, P.O. Box 7430, JOHANNESBURG 2000,

Tel. (011)470-5433, Fax. (011)470-5494

Spain: Balmes 22, 08007 BARCELONA,

Tel. (03)301 6312, Fax. (93)301 4243

Sweden: Kottbygatan 7, Akalla. S-164 85 STOCKHOLM, Tel. (0)8-632 2000, Fax. (0)8-632 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH, Tel. (01)488 2211, Fax. (01)481 7730

Talwan: 69, Min Sheng East Road, Sec 3, P.O. Box 22978, TAIPEI 10446, Tel. (2)509 7666, Fax. (2)500 5899
Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd., 60/14 MOO 11, Bangna - Trad Road Km. 3
Prakanong, BANGKOK 10260, Tel. (2)200 2000 F. (2)200 2000

Tel. (2)399-3280 to 9, (2)398-2083, Fax. (2)398-2080

Turkey: Talatpasa Cad. No. 5, 80640 LEVENT/ISTANBUL,

Tel. (01)279 2770, Fax. (01)269 3094

United Kingdom: Philips Semiconductors Limited, P.O. Box 65, Philips House, Torrington Place, LONDON, WC1E 7HD, Tel. (071)436 41 44, Fax. (071)323 03 42

**United States: INTEGRATED CIRCUITS** 

811 East Arques Avenue, SUNNYVALE, CA 94088-3409.

Tel. (01)4894 339/4894 911, Fax. (01)4814 240

Hong Kong: 15/F Philips Ind. Bldg., 24-28 Kung Yip St., KWAI CHUNG, Tel. (0)4245 121, Fax. (0)4806 960

Tel. (800)234-7381, Fax. (708)296-8556

DataSheet4U. CDISCRETE SEMICONDUCTORS: 2001 West Blue Heron Blvd., P.O. Box 10330, RIVIERA BEACH, FLORIDA 33404,

Tel. (800)447-3762 and (407)881-3200, Fax. (407)881-3300

Uruguay: Coronel Mora 433, MONTEVIDEO, Tel. (02)70-4044, Fax. (02)92 0601

For all other countries apply to: Philips Semiconductors, International Marketing and Sales, Building BAF-1, P.O. Box 218, 5600 MD, EINDHOVEN, The Netherlands. Telex 35000 phtcnl, Fax. +31-40-724825

SCD24 © Philips Electronics N.V. 1993

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property

Printed in The Netherlands

9397 723 00011

## Philips Semiconductors



